INFORMATION DISCLOSURE CITATION *(Use several sheets if necessary)*	Docket Number (Optional) NSC1-H2610	Application Number New 10/669045
	Applicant(s) Alexei Sadovnikov	
	Filing Date Herewith	Group Art Unit Unknown 2815

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Examiner	Date Considered 7/19/4

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.